







# S3D30065A S3D30065H S3D30065G S3D30065D1 650V SIC POWER SCHOTTKY RECTIFIERS

### **Description**

This 650V 30A diode is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D30065A/S3D30065H/S3D30065G/S3D30065D1 are ideal for energy sensitive, high frequency applications in challenging environments.

#### **Features**

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- · Switching speeds independent of operating temperature
- Low total conduction losses
- · High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

#### **Applications**

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- · Switching supply output rectification
- Reverse polarity protection

S3D30065A	S3D30065G	S3D30065H	S3D30065D1
1 2 K	K 2	1	1 2 3
TO-220AC	D <sup>2</sup> PAK	TO-247AC	TO-247AD
(TO-220-2)	(TO-263-2)	TO-247-2	TO-247-3
PIN 1 O	O K	1, K. Cathode 2. Anode	PIN 10——NC. PIN 20———OCASE PIN 30————







## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{DC} \end{array}$	-	650	V
	I <sub>F (AV)1</sub>	Tc=25°C	84	Α
Average Rectified Forward Current	I <sub>F (AV)2</sub>	Tc=135°C	37	Α
	I <sub>F (AV)3</sub>	Tc=146°C	30	Α
D 1311 D 1 D 1 D 1 D 1 D 1 D 1 D 1 D 1 D	I <sub>FRM1</sub>	10ms, Half Sine pulse, T <sub>C</sub> =25°C	125	Α
Repetitive Peak Forward Surge Current	I <sub>FRM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	85	Α
Peak One Cycle Non-Repetitive Surge		10ms, Half Sine pulse, T <sub>C</sub> =25°C	255	Α
Current	I <sub>FSM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	175	Α
Non-Repetitive Peak Forward Surge Current	I <sub>F,Max1</sub>	10μs. Pulse, T <sub>C</sub> =25°C	2165	Α
Guilent	I <sub>F,Max2</sub>	10μs. Pulse, T <sub>C</sub> =110°C	1490	Α
Power Dissipation	P <sub>tot1</sub> T <sub>C</sub> =25°C		246	W
	P <sub>tot2</sub>	T <sub>C</sub> =110°C	107	W

## **Electrical Characteristics:**

Characteristics	Symbol	symbol Condition		Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 30A, Pulse, T <sub>J</sub> = 25 °C	1.4	1.7	V
	V <sub>F2</sub>	@ 30A, Pulse, T <sub>J</sub> = 175 °C	1.6	2.0	V
Reverse Current at DC condition*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	4	140	uA
Reverse Current *	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 175 °C	40	400	uA
Junction Capacitance	Ст	V <sub>R</sub> =0V, T <sub>J</sub> =25°C,f=100MHz	2307	-	nF
Reverse Recovery Charge	Qc	I <sub>F</sub> = 30A, di/dt = 200A/μs VR = 400 V, T <sub>J</sub> =25°C	143.9	-	nC
Capacitance Stored Energy	Ec	V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	35.3	-	μJ

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%



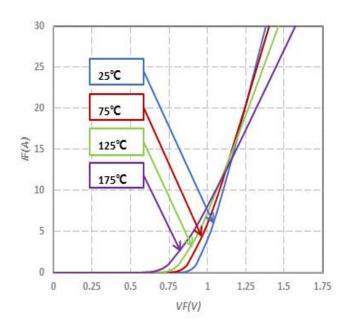




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	S3D30065A	S3D30065H	S3D30065G	S3D30065D1	Units
Junction Temperature	$T_J$		-55 to +175			°C
Storage Temperature	T <sub>stg</sub>		-55 to +175			°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	1.3	0.61	1.65	0.84(per leg) 0.42(both leg)	°C/W

## **Ratings and Characteristics Curves**



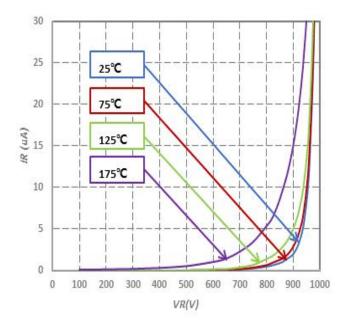


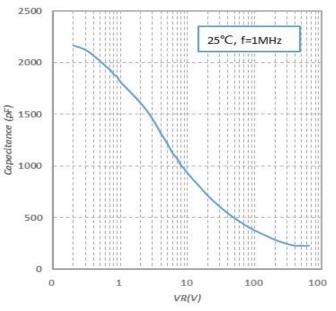
Fig.1-Typical Forward Voltage Characteristics

Fig.2-Typical Reverse Characteristics









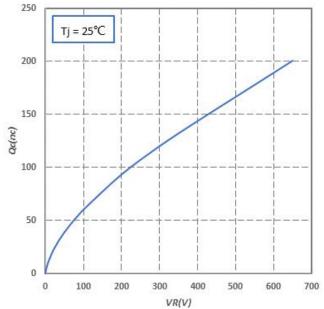
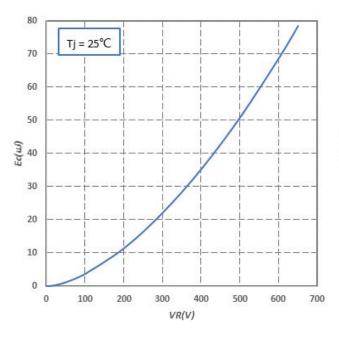


Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Total Capacitance Charge vs. Reverse Voltage



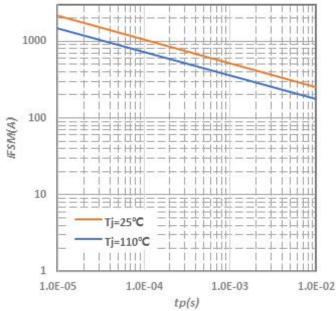


Fig.5-Capacitance Stored Energy

Fig.6-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







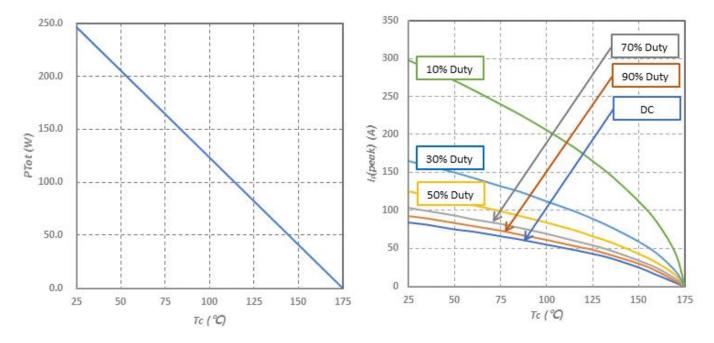
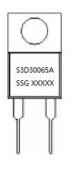


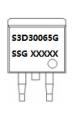
Fig.7-Power Derating

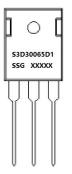
Fig.8-Current Derating

## **Marking Diagram**









Where XXXXX is YYWWL

 S3D
 = Device Type

 30
 = Forward Current (30A)

 065
 = Reverse Voltage (650V)

 A/H/G/D1
 = Package type

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

 Cautions:
 Molding resin

Epoxy resin UL:94V-0

## **Ordering Information**

Device	Package	Shipping
S3D30065A	TO-220AC(TO-220-2)	50pcs / tube
S3D30065H	TO-247AC(TO-247-2)	25pcs / tube
S3D30065G	D <sup>2</sup> PAK(TO-263-2)	800pcs / reel
S3D30065GTR	D <sup>2</sup> PAK(TO-263-2)	800pcs / reel
S3D30065D1	TO-247AD(TO-247-3)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

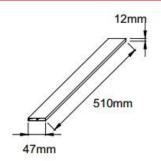
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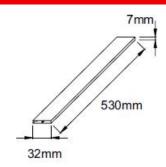






## **Tube Specification**

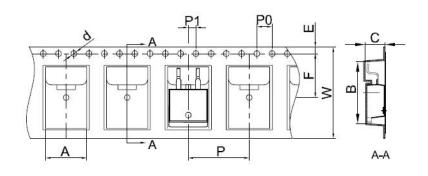




TO-247AC(TO-247-2)/TO-247AD(TO-247-3)

TO-220AC(TO-220-2)

## **Carrier Tape & Reel Specification D2PAK(TO-263-2)**



SYMBOL	Millimet	ers
STWIDOL	Min.	Max.
Α	10.70	10.90
В	16.03	16.23
С	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
Р	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

<sup>•</sup> China - Germany - Korea - Singapore - United States •

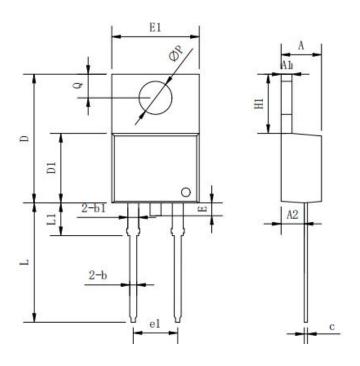
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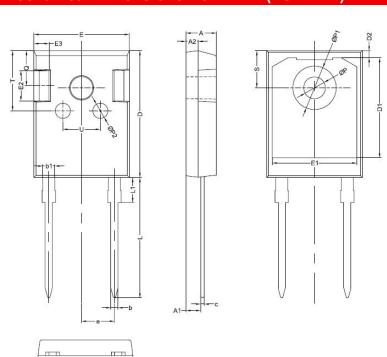


## **Mechanical Dimensions TO-220AC(TO-220-2)**



Symbol	Dimensions in millimeters			
,	Min.	Typical	Max.	
Α	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	-	-	1.78	
E1	9.65	10.16	10.67	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	-	-	6.35	
ФР	-	3.56	-	

## **Mechanical Dimensions TO-247AC(TO-247-2)**



SYMBOL	Millimeters			
STWIBOL	MIN. TYP.		MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.35	
b1	1.80	2.00	2.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.58		
D2		1.17		
E	15.60	15.80	16.00	
<u>E1</u>		14.02		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.42	
<u>L1</u>		4.13		
P	3.50	3.60	3.70	
P1	7.1	7.19	7.40	
P2		2.50		
Q		5.80		
Q S T	6.05	6.15	6.25	
T		10.00		
U		6.20		

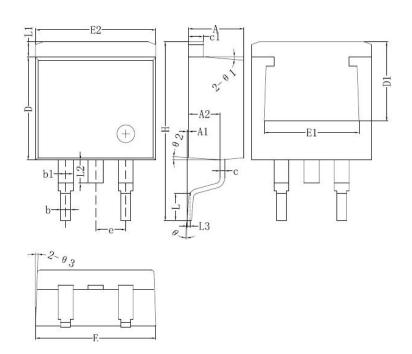
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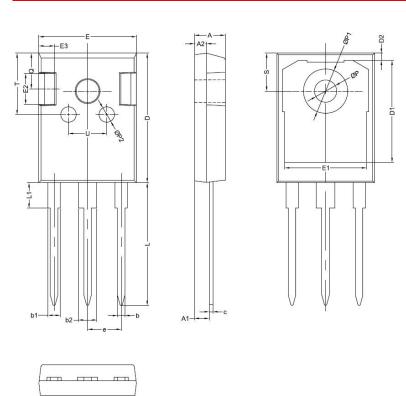


## **Mechanical Dimensions D<sup>2</sup>PAK(TO-263-2)**



Symbol	Dimensions in millimeters		
	Min.	Max.	
Α	4.06	4.83	
A1	0	0.26	
b	0.51	0.99	
b1	1.14	1.78	
С	0.31	0.74	
c1	1.14	1.65	
D	8.38	8.65	
D1	6.40		
E1	6.22		
E2	9.65	10.67	
е	2.54	BSC	
Н	14.60	15.88	
L	1.78	2.80	
L1	-	1.68	
L2	-	2.2	
L3	0.255BSC		
Θ	0	8°	

## **Mechanical Dimensions TO-247AD(TO-247-3)**



SYMBOL		Millimeters				
STIVIBUL	MIN.	TYP.	MAX.			
Α	4.80	5.00	5.20			
A1	2.20	2.41	2.61			
A2	1.90	2.00	2.10			
b	1.10	1.20	1.40			
b1	1.80	2.00	2.20			
b2	2.80	3.00	3.20			
С	0.50	0.60	0.75			
D	20.30	21.00	21.20			
D1		16.55				
D2 E		1.20				
E	15.45	15.80	16.00			
E1		13.30				
E2		5.00				
E3		2.50				
е		5.44				
L	19.42	19.92	20.70			
L1		4.13				
Р	3.50	3.60	3.70			
P1	7.1		7.40			
P2		2.50				
Q S T		5.80				
S	6.05	6.15	6.25			
T		10.00				
U		6.20				

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S3D30065A S3D30065H S3D30065G S3D30065D1



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